

Radiation-Induced Conductivity: Capacitor Discharge



Harold P. Hjalmarson
Sandia National Laboratories
Albuquerque, NM 87185

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Goal

- **Perform an initial set of calculations to explore the discharge of capacitors by ionizing radiation**

REOS: Transport, SRH Recombination and Defect Reactions

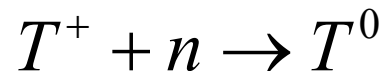
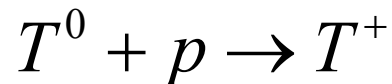
Time-dependent calculations of transport during defect reactions

Continuity Equations

$$\frac{\partial n}{\partial t} = \frac{1}{q} \nabla \bullet J_n + R_n$$

$$\frac{\partial p}{\partial t} = -\frac{1}{q} \nabla \bullet J_p + R_p$$

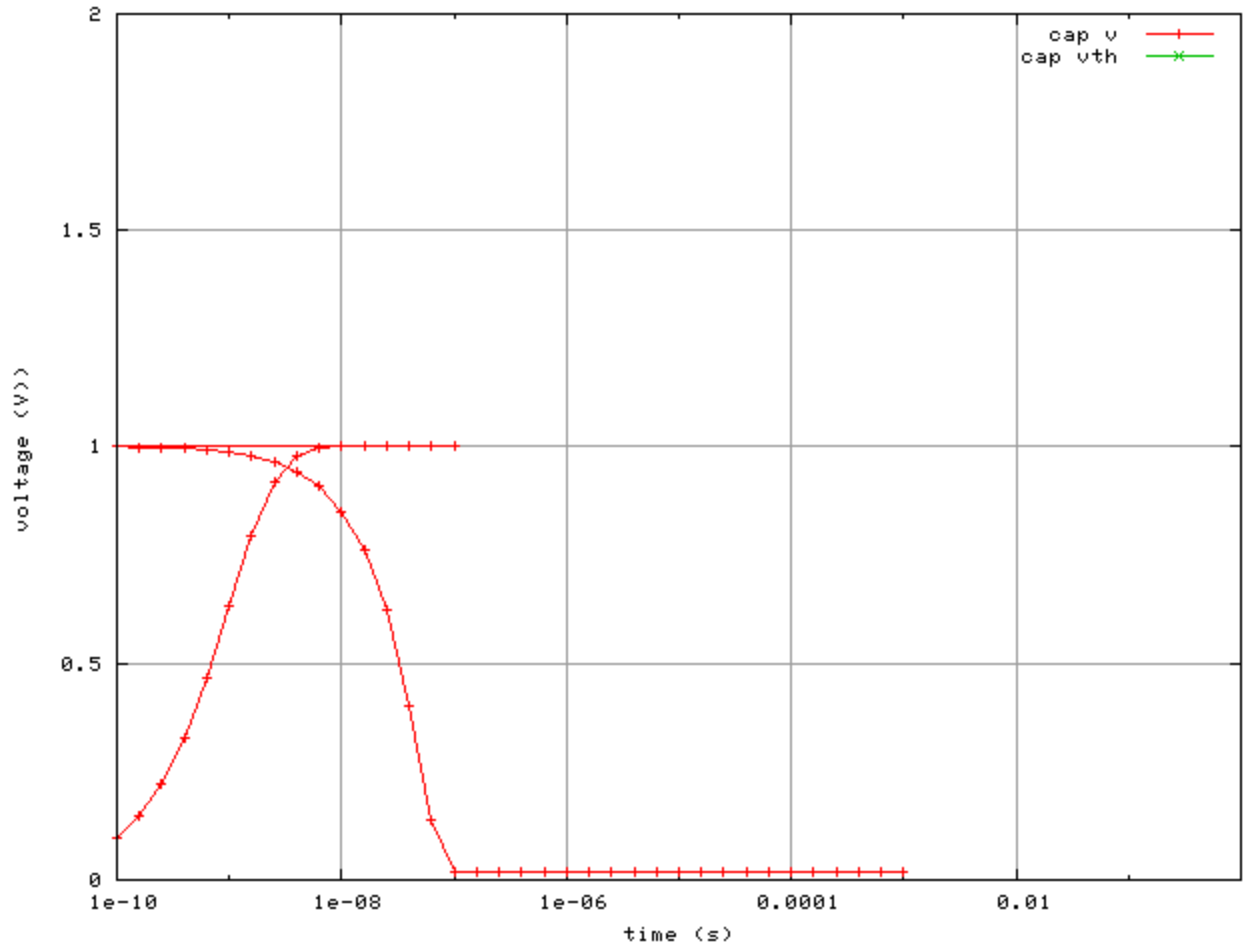
Shockley-Read-Hall (SRH) recombination



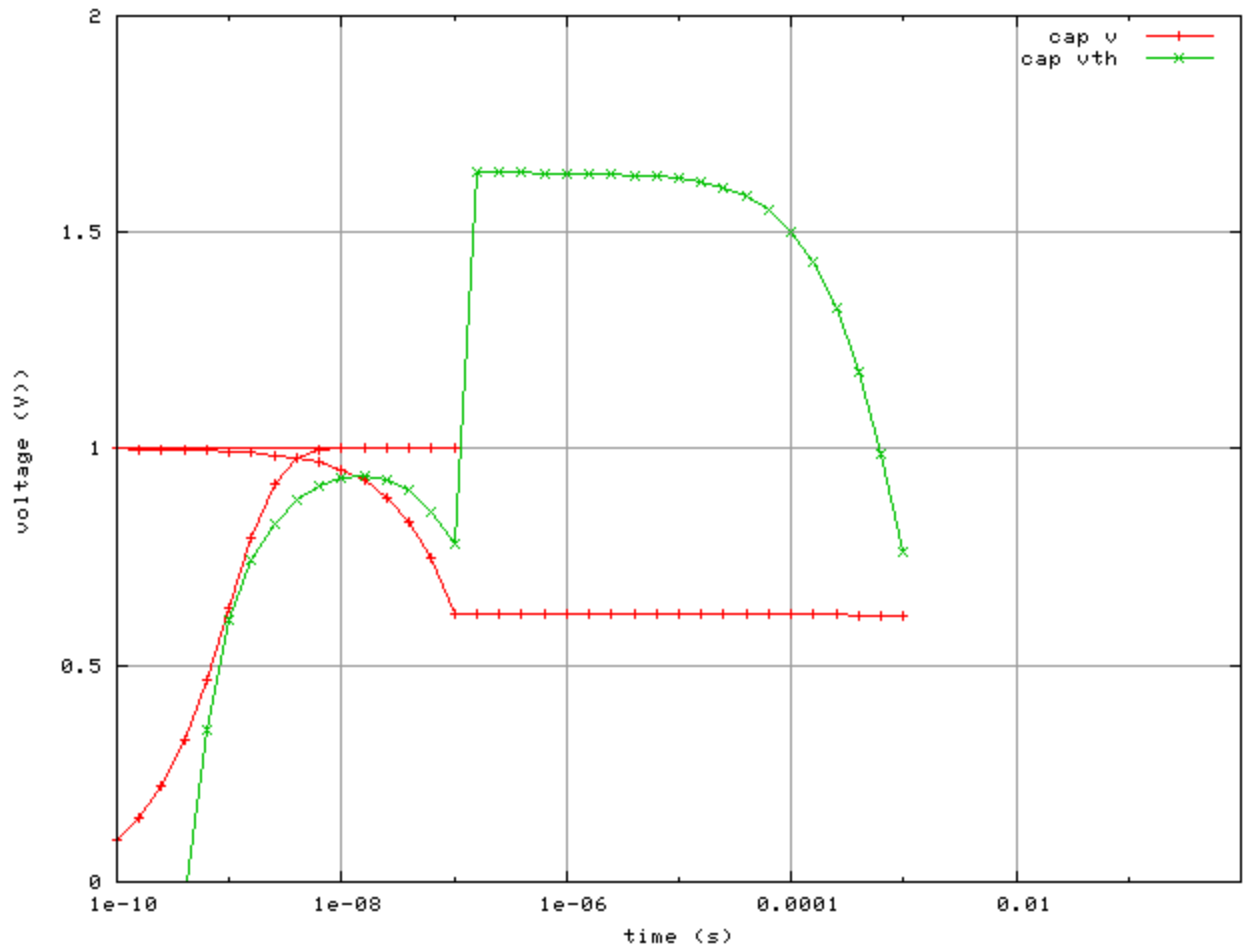
REOS Calculations

- **Structure**
 - 1 micron $1e17$ n region
 - 1 micron silicon dioxide region
 - 1 micron $1e17$ n region
- **Recombination**
 - Deep hole traps
 - SRH defects
 - Variable density
- **Radiation pulse**
 - Constant, uniform pulse of electron-hole pairs
 - Variable strength
- **Sequence of events**
 - Bias pulse: $1e-7$ s duration with 1 V bias
 - Radiation pulse: Constant pulse for $1e-8$ s with no bias and high load resistance

Capacitor Charge and Discharge: No Traps



Capacitor Charge and Discharge: With Traps



Discussion

- **No Traps**
 - **First curve**
 - » Capacitor charging to a bias of 1 V for 1e-7 s
 - **Second curve**
 - » Radiation-induced current discharges the capacitor for 1e-8 s
 - » Very slow discharge caused by load resistance leakage current
- **Traps**
 - **First curve**
 - » Capacitor charging to a bias of 1 V for 1e-7 s
 - **Second curve**
 - » Radiation-induced current discharges the capacitor for 1e-8 s
 - Current reduced by trapping and recombination at traps
 - » Slow discharge by charge released from the traps
 - » Very slow discharge caused by load resistance leakage current
 - » Threshold voltage increases when radiation ceases and then it slowly falls as traps release holes

Summary

- **Two effects**
 - RIC during irradiation
 - Trap emission
- **Next**
 - Check threshold voltage validity